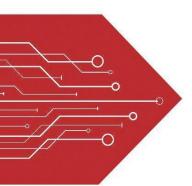
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet





FEATURES

- For surface mounted applications
- Glass Passivated Chip Junction
- Fast reverse recovery time
- Ideal for automated placement





SOD-323

PINNING

MARK:T3

PIN	DESCRIPTION	
1	Cathode	
2	Anode	

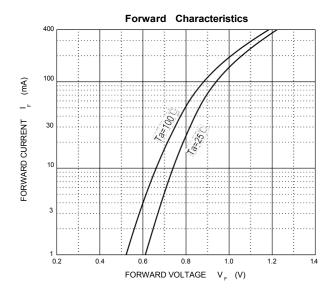
Absolute Maximum Ratings at 25 °C

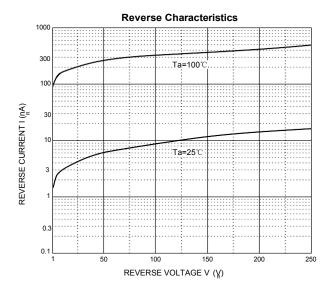
Parameter		BAV21WS	Units
Maximum Repetitive Peak Reverse Voltage		250	V
Maximum RMS voltage		200	V
Continuous Forward Current		250	mA
Repetitive Peak Forward Current		625	mA
at 1 Non-reptitive Peak Forward Surge Current at 1 at 1	ms I _{FSM}	1 3 9	А
Total Power Dissipation		500	mW
Operating and Storage Temperature Range		-55 ~ +150	°C

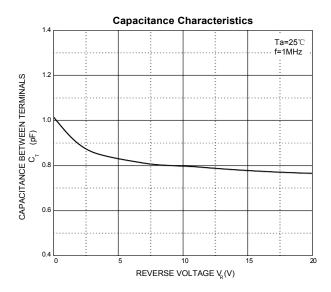
Characteristics at T_a = 25 °C

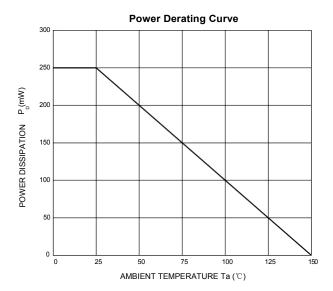
Parameter	Symbols	BAV21WS	Units
Reverse BreakdownVoltage at I _R =100µA	$V_{(BR)R}$	250	V
Maximum Forward Voltage at 100 mA at 200 mA	V _F	1.00 1.25	V
Maximum DCReverse Current T _a = 25 °C at Rated DCBlocking Voltage T _a =150 °C	I _R	0.1 100	μΑ
Typical Junction Capacitance at V _R =4V, f=1MHz	C _j	5	pF
Maximum Reverse Recovery Time (1)	t _{rr}	50	ns







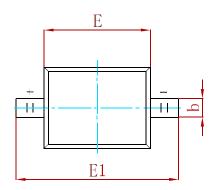


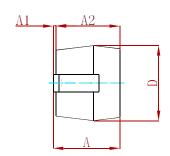


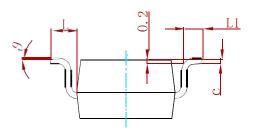






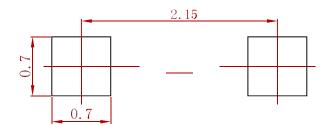






Symbol	Dimensions	In Millimeters	Dimensions In Inches	
	Min.	Max.	Min.	Max.
Α		1.000		0.039
A 1	0.000	0.100	0.000	0.004
A2	0.800	0.900	0.031	0.035
b	0.250	0.350	0.010	0.014
С	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.550	2.750	0.100	0.108
L	0.475 REF.		0.019	REF.
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BAV21WS-MS	SOD-323	3000



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